

L Number	Hits	Search Text	DB	Time stamp
-	206	III-V and pattern\$3 same (width or diameter or length) and overla\$3 and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 15:29
-	30	III-V and pattern\$3 same (width or diameter or length) same overla\$3 and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 15:34
-	36	III-V and pattern\$3 same (width or diameter or length) same second and overla\$3 and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 15:36
-	11	III-V and pattern\$3 same displac\$3 and overla\$3 and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 15:41
-	16	III-V and pattern\$3 same off\$1set and overla\$3 and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:00
-	222	semiconductor and pattern\$3 same off\$1set same overla\$3 and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:08
-	20	semiconductor and pattern\$3 same off\$1set same overla\$3 and @py<2002 and buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:13
-	55	pattern\$3 same off\$1set same overla\$3 and @py<2002 and (117/\$4.ccls or 438/\$4.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:16
-	97	pattern\$3 and window near4 overla\$3 and @py<2002 and (117/\$4.ccls or 438/\$4.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:21
-	15	pattern\$3 and window near4 off\$1set and @py<2002 and (117/\$4.ccls or 438/\$4.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:25
-	43	ELO and III-V	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/23 09:54
-	177	III-V and sacrific\$4 near3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/23 11:11
-	34	III-V and pattern\$3 same two near3 direction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/23 11:41

-	91	III-V and pattern\$3 same pitch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/23 16:15
-	70	III-V and pattern\$3 same mask same strip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/23 16:17
-	39	III-V and pattern\$3 and pitch same var\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/23 16:29
-	19	III-V and pattern\$3 and pitch same vary\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 09:49
-	21	III-V and pitch same vary\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/23 16:35
-	10	III-V and pitch same variable	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 09:47
-	29	III-V and mask\$3 same (strip and window)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 09:48
-	59	III-V and pattern\$3 same mask same two same (direction or dimension)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 09:53
-	14	III-V and pattern\$3 same mask same two near3 (direction or dimension)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 09:58
-	61	III-V and pattern\$3 same two near3 (direction or dimension)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 10:04
-	17	III-V and checker\$1board	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 10:59
-	120	selective adj deposit\$3 same (silica or sio2 or "sio.sub.2" or oxide or dioxide) same mask\$3 and (117/\$4.ccls. or 438/\$4.ccls.) and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:32
-	52	selective adj deposit\$3 near3 (silica or sio2 or "sio.sub.2" or oxide or dioxide) and (117/\$4.ccls. or 438/\$4.ccls.) and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:36
-	253	offset and etch\$3 and III-V and pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 14:06

-	37	offset same etch\$3 and III-V and pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 14:39
-	159	diode adj laser adj bar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 14:39
-	33	III-V and pattern\$3 same misalign\$4 and mask\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 15:32